

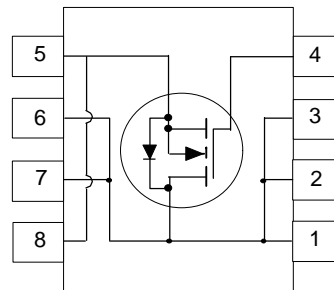
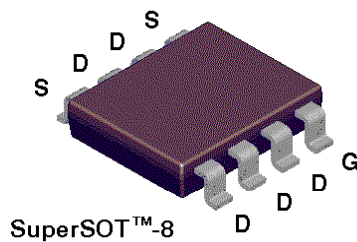
## NDH831N N-Channel Enhancement Mode Field Effect Transistor

### General Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, high cell density, DMOS technology. This very high density process is especially tailored to minimize on-state resistance and provide superior switching performance. These devices are particularly suited for low voltage applications such as notebook computer power management and portable electronics where fast switching, low in-line power loss, and resistance to transients are needed.

### Features

- 5.8A, 20V.  $R_{DS(ON)} = 0.03\Omega @ V_{GS} = 4.5V$   
 $R_{DS(ON)} = 0.04\Omega @ V_{GS} = 2.7V$ .
- High density cell design for extremely low  $R_{DS(ON)}$ .
- Enhanced SuperSOT™-8 small outline surface mount package with high power and current handling capability.



### Absolute Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter		NDH831N	Units
$V_{DSS}$	Drain-Source Voltage		20	V
$V_{GSS}$	Gate-Source Voltage		8	V
$I_D$	Drain Current - Continuous	(Note 1a)	5.8	A
	- Pulsed		20	
$P_D$	Maximum Power Dissipation	(Note 1a)	1.8	W
		(Note 1b)	1	
		(Note 1c)	0.9	
$T_J, T_{STG}$	Operating and Storage Temperature Range		-55 to 150	$^\circ\text{C}$

### THERMAL CHARACTERISTICS

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	70	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	(Note 1)	20	$^\circ\text{C/W}$

**ELECTRICAL CHARACTERISTICS** ( $T_A = 25^\circ\text{C}$  unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units	
<b>OFF CHARACTERISTICS</b>							
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	20			V	
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 16\text{ V}, V_{GS} = 0\text{ V}$			1	$\mu\text{A}$	
			$T_J = 55^\circ\text{C}$		10	$\mu\text{A}$	
$I_{GSSF}$	Gate - Body Leakage, Forward	$V_{GS} = 8\text{ V}, V_{DS} = 0\text{ V}$			100	nA	
$I_{GSSR}$	Gate - Body Leakage, Reverse	$V_{GS} = -8\text{ V}, V_{DS} = 0\text{ V}$			-100	nA	
<b>ON CHARACTERISTICS</b> (Note 2)							
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$		0.4	0.6	1	V
			$T_J = 125^\circ\text{C}$	0.3	0.35	0.8	
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 4.5\text{ V}, I_D = 5.8\text{ A}$			0.022	0.03	W
			$T_J = 125^\circ\text{C}$		0.03	0.54	
			$V_{GS} = 2.7\text{ V}, I_D = 5\text{ A}$		0.027	0.04	
$I_{D(on)}$	On-State Drain Current	$V_{GS} = 4.5\text{ V}, V_{DS} = 5\text{ V}$	20			A	
			$V_{GS} = 2.7\text{ V}, V_{DS} = 5\text{ V}$	5			
$g_{FS}$	Forward Transconductance	$V_{DS} = 10\text{ V}, I_D = 5.8\text{ A}$		14		S	
<b>DYNAMIC CHARACTERISTICS</b>							
$C_{iss}$	Input Capacitance	$V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$		720		pF	
$C_{oss}$	Output Capacitance			430		pF	
$C_{rss}$	Reverse Transfer Capacitance			155		pF	
<b>SWITCHING CHARACTERISTICS</b> (Note 2)							
$t_{D(on)}$	Turn - On Delay Time	$V_{DD} = 6\text{ V}, I_D = 1\text{ A},$ $V_{GEN} = 4.5\text{ V}, R_{GEN} = 6\ \Omega$		10	20	ns	
$t_r$	Turn - On Rise Time			30	50	ns	
$t_{D(off)}$	Turn - Off Delay Time			55	80	ns	
$t_f$	Turn - Off Fall Time			20	40	ns	
$Q_g$	Total Gate Charge		$V_{DS} = 5\text{ V},$ $I_D = 5.8\text{ A}, V_{GS} = 4.5\text{ V}$		19.5	28	nC
$Q_{gs}$	Gate-Source Charge			1.8		nC	
$Q_{gd}$	Gate-Drain Charge			5.5		nC	

**ELECTRICAL CHARACTERISTICS** ( $T_A = 25^\circ\text{C}$  unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS</b>						
$I_S$	Maximum Continuous Drain-Source Diode Forward Current				1.5	A
$V_{SD}$	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}$ , $I_S = 1.5\text{ A}$ (Note 2)		0.75	1.2	V

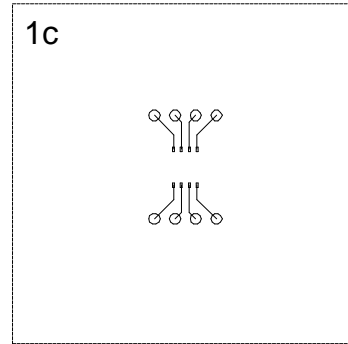
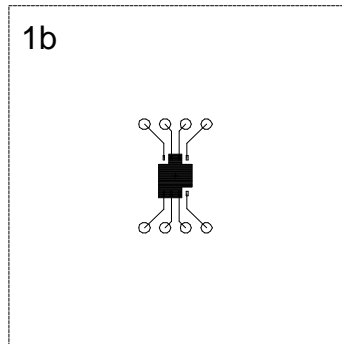
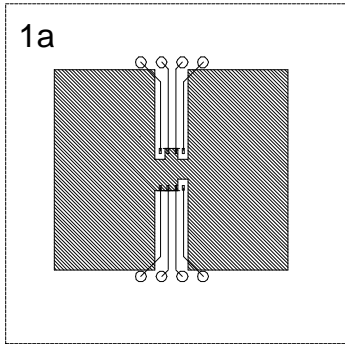
Notes:

- $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.

$$P_D(t) = \frac{T_J - T_A}{R_{\theta J A}(t)} = \frac{T_J - T_A}{R_{\theta J C} + R_{\theta CA}(t)} = I_D^2(t) \times R_{DS(on)} \theta_{TJ}$$

Typical  $R_{\theta JA}$  using the board layouts shown below on 4.5"x5" FR-4 PCB in a still air environment:

- 70°C/W when mounted on a 1 in<sup>2</sup> pad of 2oz copper.
- 125°C/W when mounted on a 0.026 in<sup>2</sup> pad of 2oz copper.
- 135°C/W when mounted on a 0.005 in<sup>2</sup> pad of 2oz copper.



Scale 1 : 1 on letter size paper

- Pulse Test: Pulse Width  $\leq 300\mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ .

## Typical Electrical Characteristics

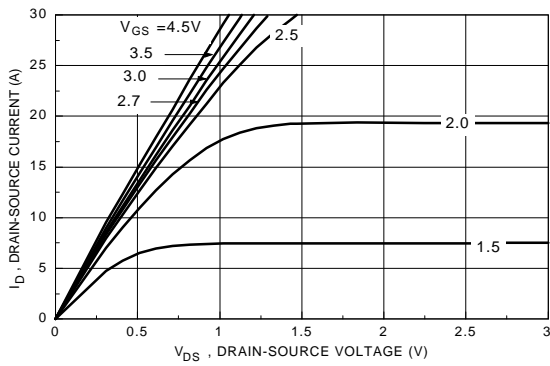


Figure 1. On-Region Characteristics.

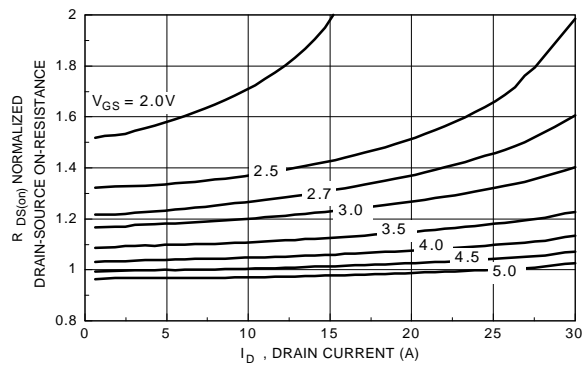


Figure 2. On-Resistance Variation with Gate Voltage and Drain Current.

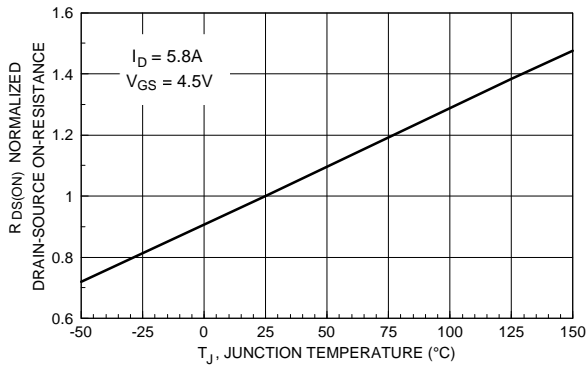


Figure 3. On-Resistance Variation with Temperature.

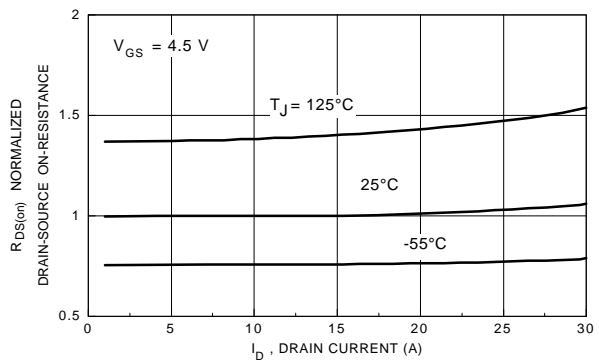


Figure 4. On-Resistance Variation with Drain Current and Temperature.

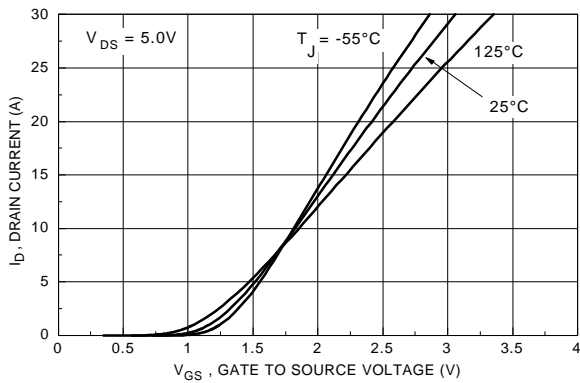


Figure 5. Transfer Characteristics.

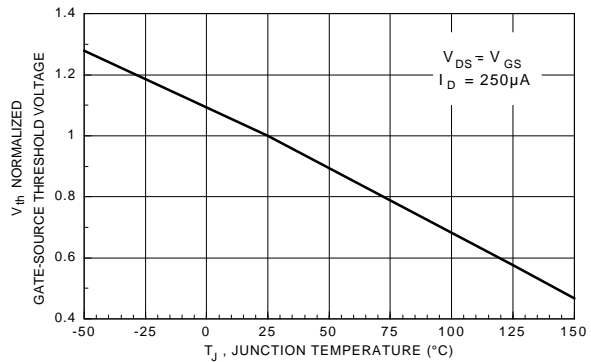
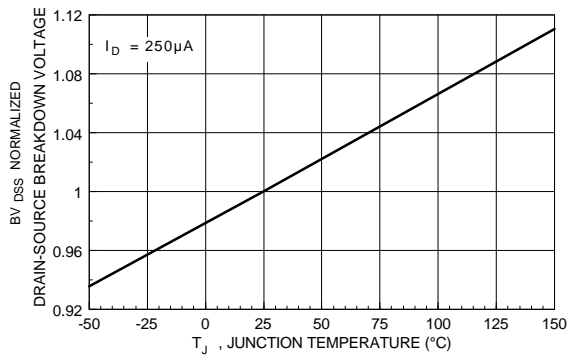
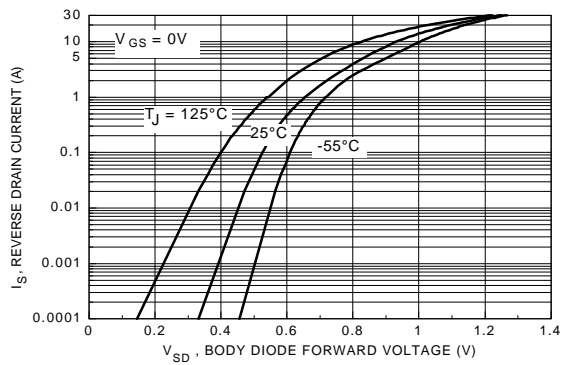


Figure 6. Gate Threshold Variation with Temperature.

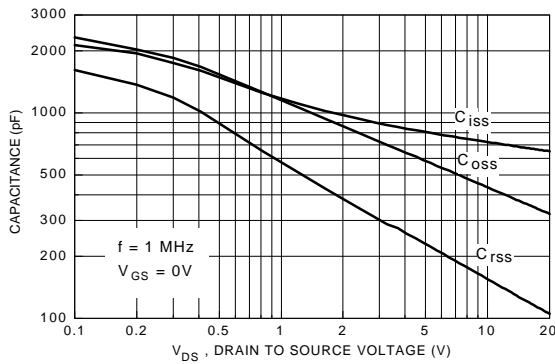
## Typical Electrical Characteristics



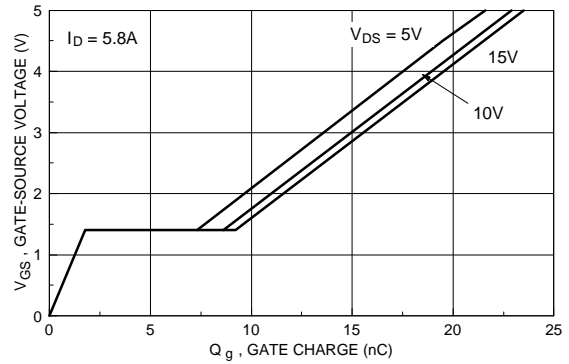
**Figure 7. Breakdown Voltage Variation with Temperature.**



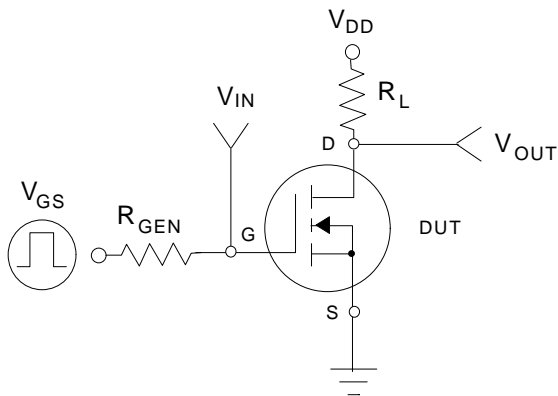
**Figure 8. Body Diode Forward Voltage Variation with Current and Temperature.**



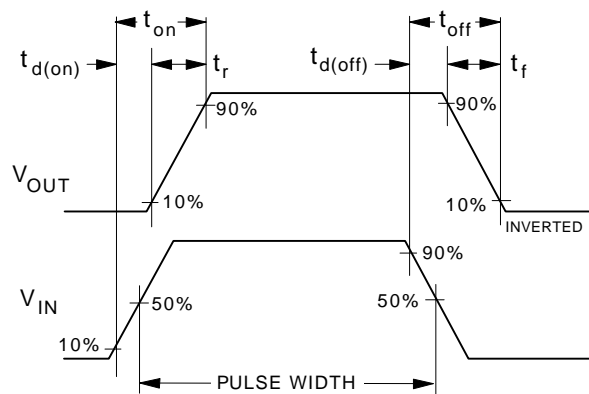
**Figure 9. Capacitance Characteristics.**



**Figure 10. Gate Charge Characteristics.**



**Figure 11. Switching Test Circuit**



**Figure 12. Switching Waveforms**

## Typical Thermal Characteristics

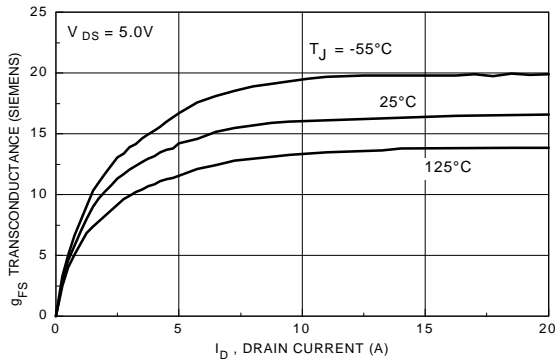


Figure 13. Transconductance Variation with Drain Current and Temperature.

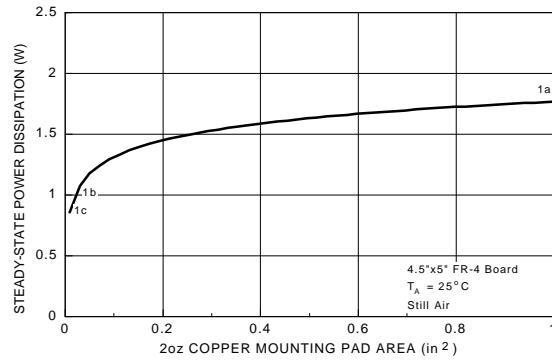


Figure 14. SuperSOT™-8 Maximum Steady-State Power Dissipation versus Copper Mounting Pad Area.

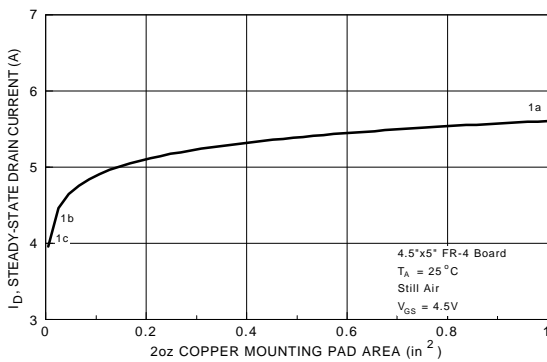


Figure 15. Maximum Steady-State Drain Current versus Copper Mounting Pad Area.

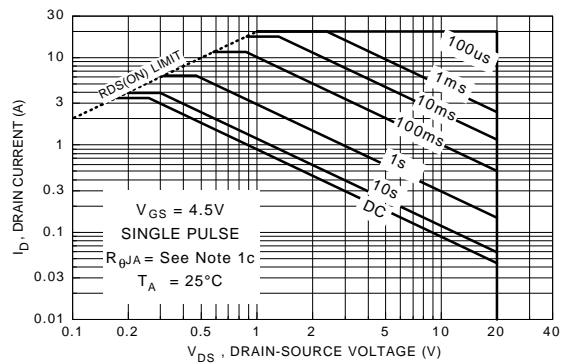


Figure 16. Maximum Safe Operating Area.

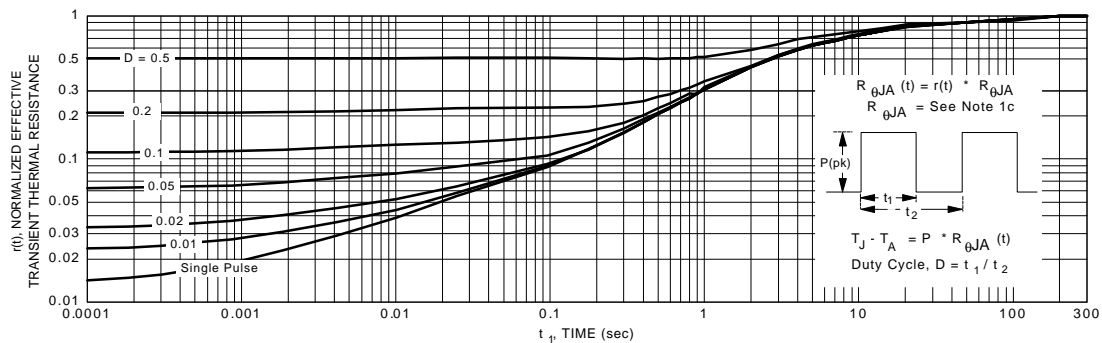


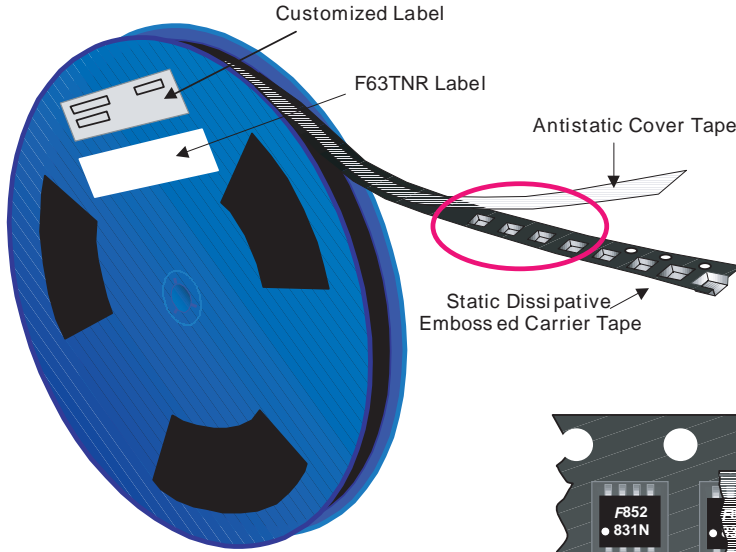
Figure 17. Transient Thermal Response Curve.

Note: Thermal characterization performed using the conditions described in note 1c. Transient thermal response will change depending on the circuit board design.

# SuperSOT™-8 Tape and Reel Data and Package Dimensions



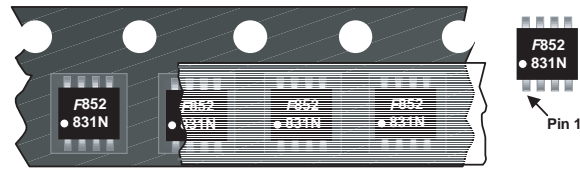
## SSOT-8 Packaging Configuration: Figure 1.0



### Packaging Description:

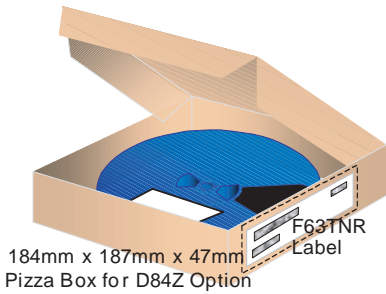
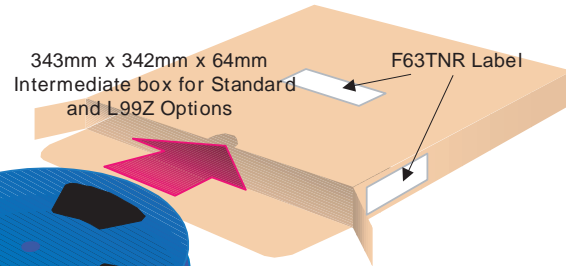
SSOT-8 parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 3,000 units per 13" or 330cm diameter reel. The reels are dark blue in color and is made of polystyrene plastic (anti-static coated). Other option comes in 500 units per 7" or 177cm diameter reel. This and some other options are further described in the Packaging Information table.

These full reels are individually barcode labeled and placed inside a standard intermediate box (illustrated in figure 1.0) made of recyclable corrugated brown paper. One box contains two reels maximum. And these boxes are placed inside a barcode labeled shipping box which comes in different sizes depending on the number of parts shipped.



### SSOT-8 Unit Orientation

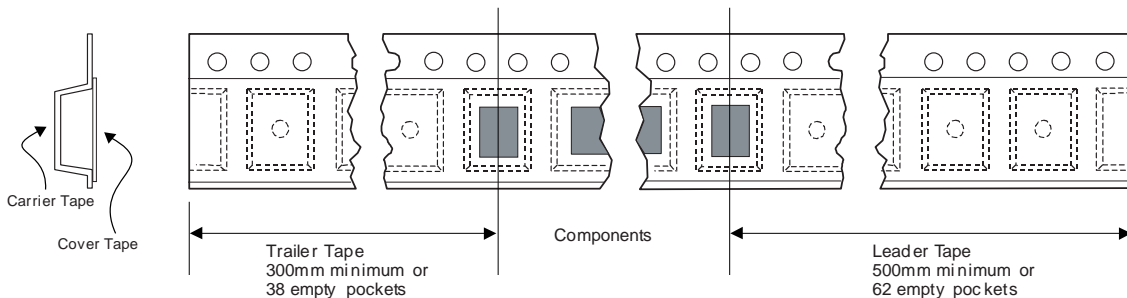
SSOT-8 Packaging Information		
Packaging Option	Standard (no flow code)	D84Z
Packaging type	TNR	TNR
Qty per Reel/Tube/Bag	3,000	500
Reel Size	13" Dia	7" Dia
Box Dimension (mm)	343x64x343	184x187x47
Max qty per Box	6,000	1,000
Weight per unit (gm)	0.0416	0.0416
Weight per Reel (kg)	0.5615	0.0980
Note/Comments		



### F63TNR Label sample

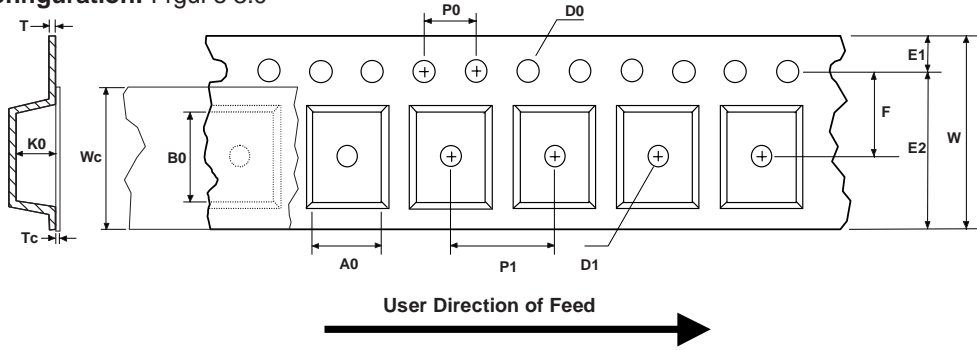


## SSOT-8 Tape Leader and Trailer Configuration: Figure 2.0



# SuperSOT™-8 Tape and Reel Data and Package Dimensions, continued

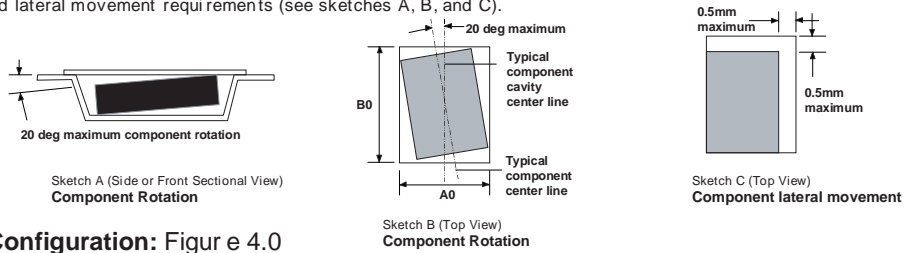
## SSOT-8 Embossed Carrier Tape Configuration: Figure 3.0



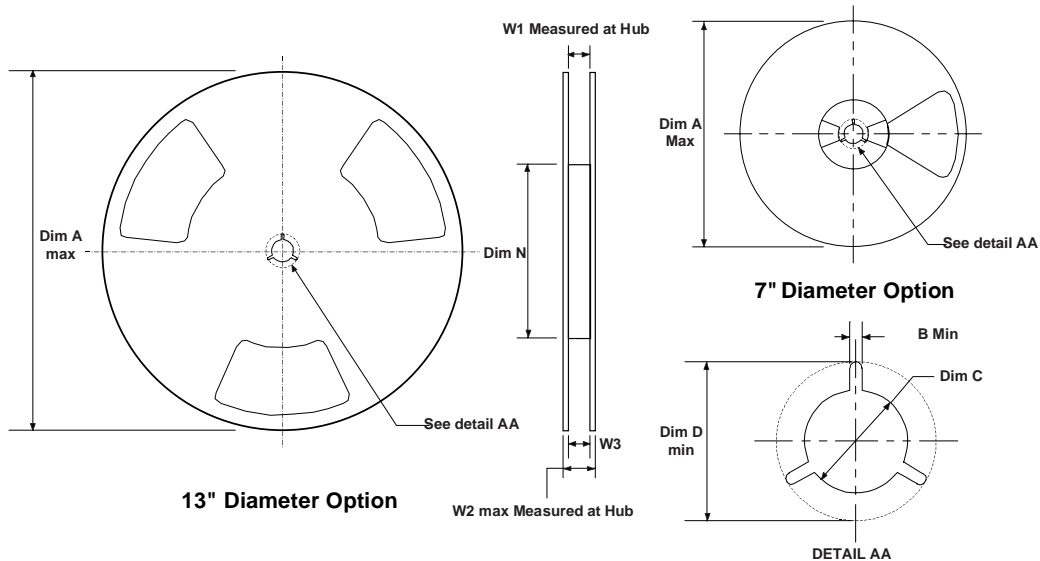
Dimensions are in millimeter

Pkg type	A0	B0	W	D0	D1	E1	E2	F	P1	P0	K0	T	Wc	Tc
SSOT-8 (12mm)	4.47 +/-0.10	5.00 +/-0.10	12.0 +/-0.3	1.55 +/-0.05	1.50 +/-0.10	1.75 +/-0.10	10.25 min	5.50 +/-0.05	8.0 +/-0.1	4.0 +/-0.1	1.37 +/-0.10	0.280 +/-0.150	9.5 +/-0.025	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



## SSOT-8 Reel Configuration: Figure 4.0



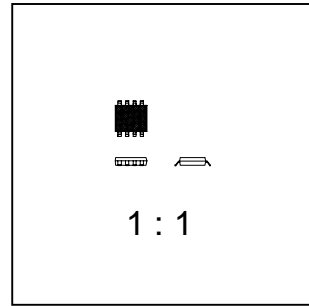
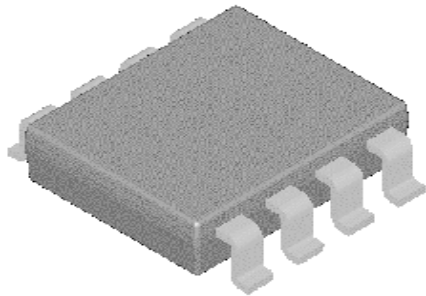
Dimensions are in inches and millimeters

Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
12mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	5.906 150	0.488 +0.078/-0.000 12.4 +20	0.724 18.4	0.469 - 0.606 11.9 - 15.4
12mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	7.00 178	0.488 +0.078/-0.000 12.4 +20	0.724 18.4	0.469 - 0.606 11.9 - 15.4



# SuperSOT™-8 Tape and Reel Data and Package Dimensions, continued

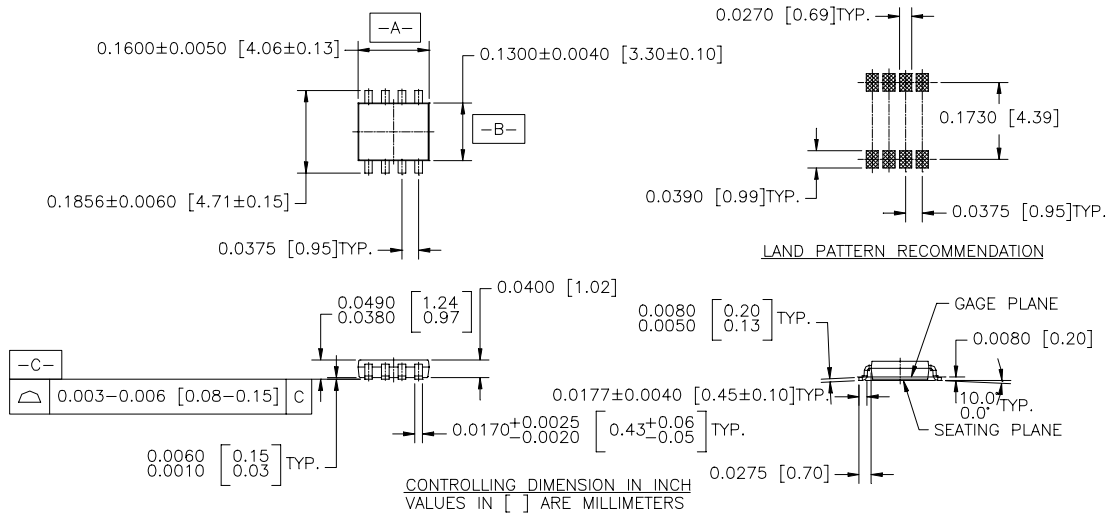
## SuperSOT™-8 (FS PKG Code 34, 35)



Scale 1:1 on letter size paper

Dimensions shown below are in:  
inches [millimeters]

Part Weight per unit (gram): 0.0416



NOTES : UNLESS OTHERWISE SPECIFIED

- STANDARD LEAD FINISH TO BE 200 MICRONS / 5.08 MICROMETERS MINIMUM TIN/LEAD (SOLDER) ON COPPER.
- NO JEDEC REGISTRATION AS JAN. 1996

SUPER SOT, 8 LEADS

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E <sup>2</sup> CMOS™	PowerTrench®	VCX™
FACT™	QFET™	
FACT Quiet Series™	QS™	
FAST®	Quiet Series™	
FASTr™	SuperSOT™-3	
GTO™	SuperSOT™-6	
HiSeC™	SuperSOT™-8	

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### Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.